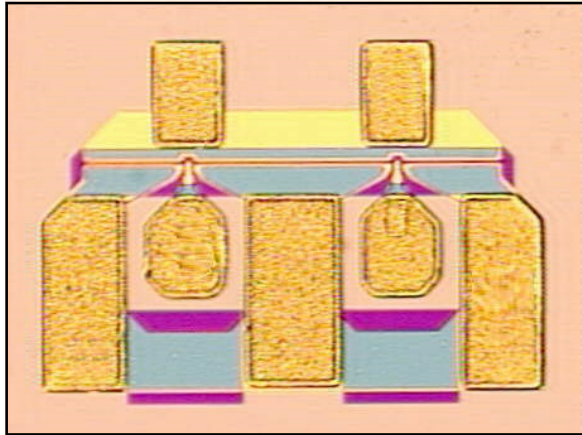


300um Discrete pHEMT TGF4350-EPU

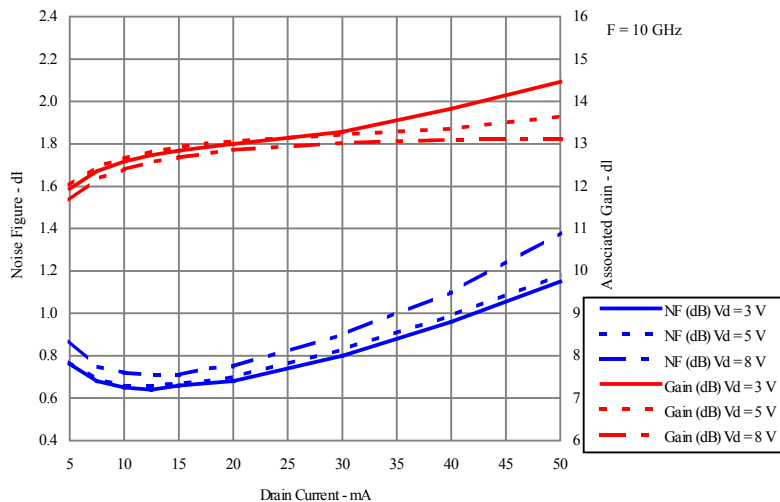
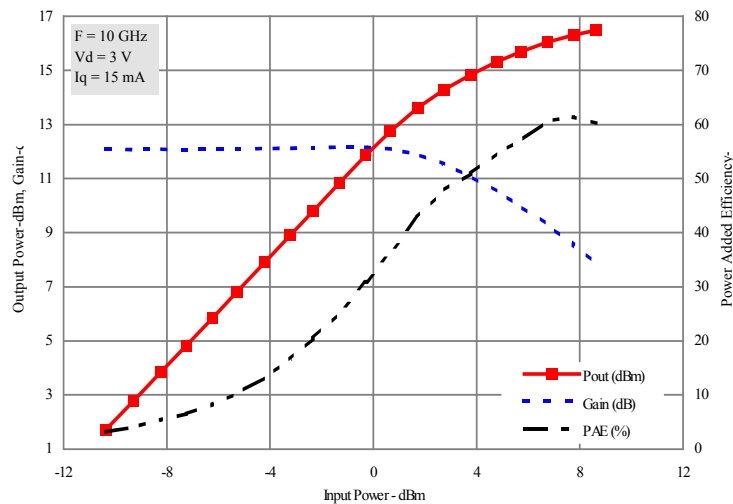


Key Features and Performance

- 0.25um pHEMT Technology
- DC 22 GHz Frequency Range
- 1.2 dB NF, 14.5 dB Associated Gain at 10 GHz, 3V Operation
- Floating Source Configuration
- Chip Dimensions 0.5080 mm x 0.4064 mm

Primary Applications

- Low Noise amplifiers



Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications subject to change without notice

Electrical Characteristics

RECOMMENDED MAXIMUM RATINGS

Symbol	Parameter	Value	Notes
V ⁺	Positive Supply Voltage	7 V	
I ⁺	Positive Supply Current	.085A	<u>3/</u>
P _D	Power Dissipation	0.6 W	
P _{IN}	Input Continuous Wave Power	20 dBm	
T _{CH}	Operating Channel Temperature	150 °C	<u>1/</u> , <u>2/</u>
T _M	Mounting Temperature (30 seconds)	320 °C	
T _{STG}	Storage Temperature	-65 °C to 150 °C	

- 1/ These ratings apply to individual FET
- 2/ Junction operating temperature will directly affect the device mean time to failure (MTTF). For maximum life it is recommended that junction temperatures be maintained at the lowest possible levels.
- 3/ Nominal value of Idss

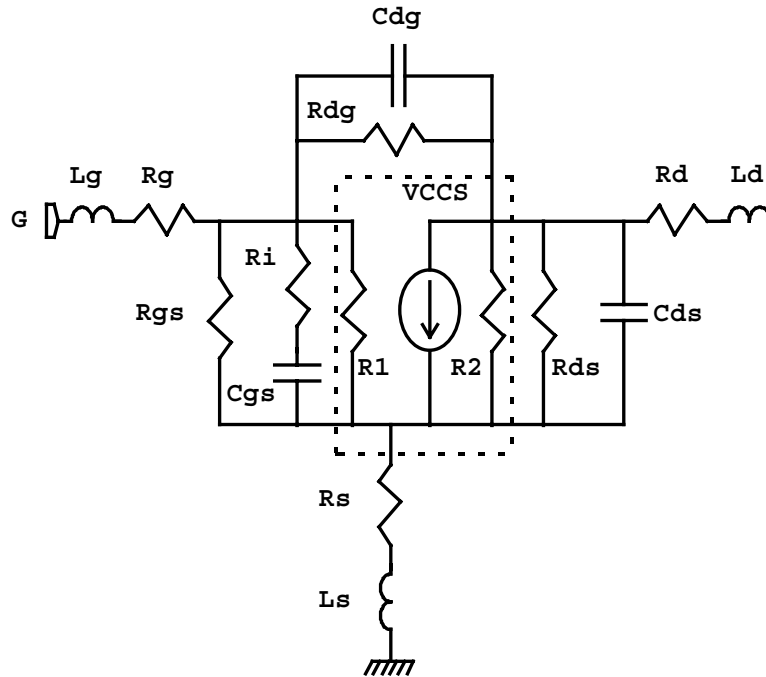
 DC PROBE TESTS
 (T_A = 25 °C ± 5°C)

Symbol	Parameter	Minimum	Maximum	Value
Idss	Saturated Drain Current (info only)	30	141	mA
V _{P1-5}	Pinch-off Voltage	-1.5	-0.5	V
BV _{GS1}	Breakdown Voltage gate-source	-30	-8	V
BV _{GD1-5}	Breakdown Voltage gate-drain	-30	-8	V

Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice.

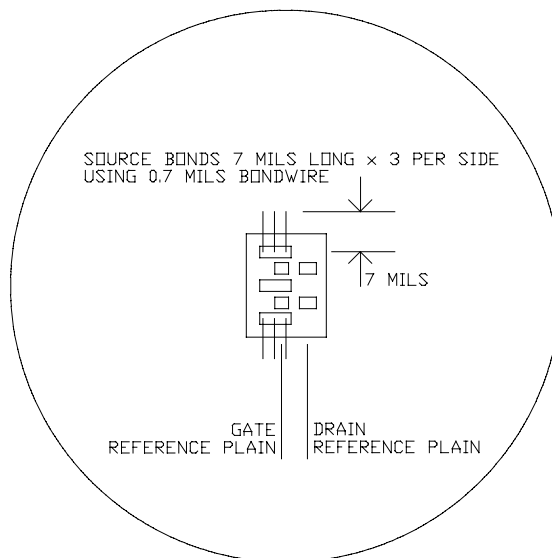
FET Elements

- Lg = 0.040 nH
- Rg = 0.525 Ohms
- Rgs = 14500 Ohms
- Ri = 4.924 Ohms
- Cgs = 0.364 pF
- Cdg = 0.042 pF
- Rdg = 146000 Ohms
- Rs = 0.300 Ohms
- Ls = 0.041 nH
- Rds = 253.858 Ohms
- Cds = 0.080 pF
- Rd = 0.833 Ohms
- Ld = 0.028 nH
- VCCS Parameters
- M = 0.091 S
- A = 0
- R1 = 1E19 Ohms
- R2 = 1E19 Ohms
- F = 0
- T = 4.000 pS

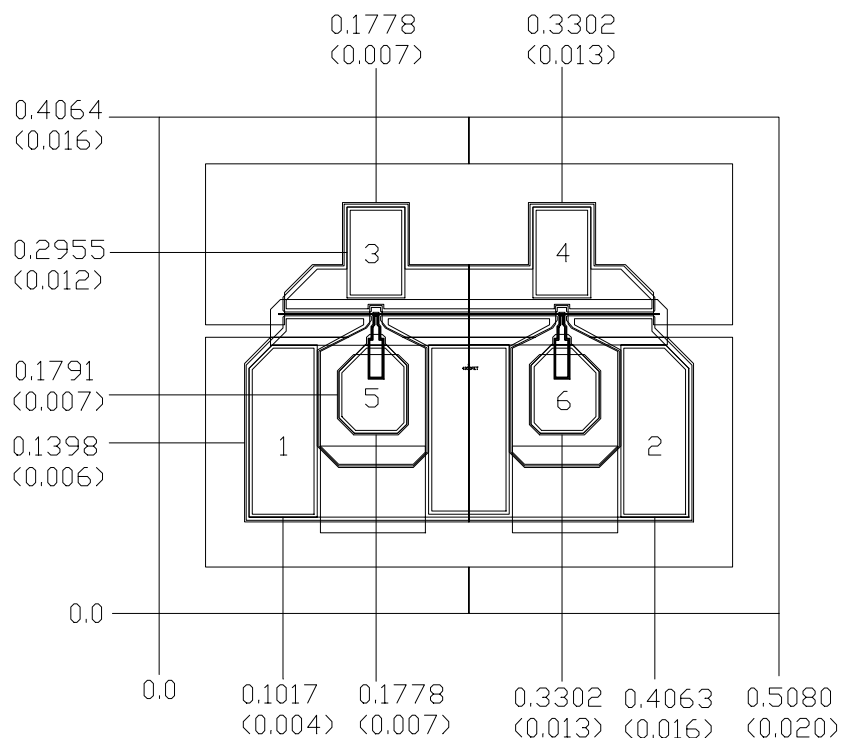


TGA4350EPU pHEMT Model (Vds = 3.0 V and 15mA at T = 25°C)

Device is mounted on a 20 mil high ledge. Source inductance includes that of source bondwires and ledge



Mechanical Drawing



Units: millimeters (inches)

Thickness: 0.1016 (0.004)

Chip edge to bond pad dimensions are shown to center of bond pad
chip size tolerance: +/- 0.051 (0.002)

Bond Pad #1,#2 (Source)	0.051 x 0.136 (0.002 x 0.005)
Bond Pad #3,#4 (Drain)	0.042 x 0.069 (0.002 x 0.003)
Bond Pad #5,#6 (Gate)	0.051 x 0.067 (0.002 x 0.003)

Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice.

Process and Assembly Notes

***This device should be attached using conductive epoxy only.
Contact factory for additional details as required.***

Component placement and adhesive attachment assembly notes:

- vacuum pencils and/or vacuum collets preferred method of pick up
- avoidance of air bridges during placement
- force impact critical during auto placement
- organic attachment can be used in low-power applications
- curing should be done in a convection oven; proper exhaust is a safety concern
- microwave or radiant curing should not be used because of differential heating
- coefficient of thermal expansion matching is critical

Interconnect process assembly notes:

- thermosonic ball bonding is the preferred interconnect technique
- force, time, and ultrasonics are critical parameters
- aluminum wire should not be used
- discrete FET devices with small pad sizes should be bonded with 0.0007-inch wire
- maximum stage temperature: 200°C

GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.